



RN2422TE85LF Information



For Reference Only

Part Number RN2422TE85LF

Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single, Pre-Biased

Description TRANS PREBIAS PNP 200MW SMINI

Package TO-236-3, SC-59, SOT-23-3
For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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RN2422TE85LF Specifications

Manufacturer Part NumberRN2422TE85LFManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsPackageTO-236-3, SC-59, SOT-23-3Series-Transistor TypePNP - Pre-BiasedCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)2.2kResistor - Emitter Base (R2) (Ohms)2.2kDC Current Gain (hFE) (Min) @ Ic, Vce65 @ 100mA, 1VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition200MHzPower - Max200mWMounting TypeSurface MountPackage / CaseTO-236-3, SC-59, SOT-23-3Supplier Device PackageS-Mini	•	
Category Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single, Pre-Biased Package TO-236-3, SC-59, SOT-23-3 Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Manufacturer Part Number	RN2422TE85LF
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Package TO-236-3, SC-59, SOT-23-3 Series Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vee Saturation (Max) @ Ib, Ic 250mV @ 1mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package	Category	Discrete Semiconductor Products
Series - PNP - Pre-Biased Current - Collector (Ic) (Max) 800mA Voltage - Collector Emitter Breakdown (Max) 50V Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) 2.2k DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic 250mV @ 1mA, 50mA Current - Collector Cutoff (Max) 500nA Frequency - Transition 200MHz Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini		Transistors - Bipolar (BJT) - Single, Pre-Biased
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Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package	Series	-
Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic 250mV @ 1mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Transistor Type	PNP - Pre-Biased
Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition Power - Max Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package	Current - Collector (Ic) (Max)	800mA
Resistor - Emitter Base (R2) (Ohms) 2.2k DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic 250mV @ 1mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Voltage - Collector Emitter Breakdown (Max)	50V
DC Current Gain (hFE) (Min) @ Ic, Vce 65 @ 100mA, 1V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 200MHz Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Resistor - Base (R1) (Ohms)	2.2k
Vce Saturation (Max) @ Ib, Ic250mV @ 1mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition200MHzPower - Max200mWMounting TypeSurface MountPackage / CaseTO-236-3, SC-59, SOT-23-3Supplier Device PackageS-Mini	Resistor - Emitter Base (R2) (Ohms)	2.2k
Current - Collector Cutoff (Max) Frequency - Transition Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	DC Current Gain (hFE) (Min) @ Ic, Vce	65 @ 100mA, 1V
Frequency - Transition 200MHz Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Vce Saturation (Max) @ Ib, Ic	250mV @ 1mA, 50mA
Power - Max 200mW Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Current - Collector Cutoff (Max)	500nA
Mounting Type Surface Mount Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Frequency - Transition	200MHz
Package / Case TO-236-3, SC-59, SOT-23-3 Supplier Device Package S-Mini	Power - Max	200mW
Supplier Device Package S-Mini	Mounting Type	Surface Mount
	Package / Case	TO-236-3, SC-59, SOT-23-3
Report errors?	Supplier Device Package	S-Mini
		Report errors?

RN2422TE85LF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

RN2422TE85LF Payment Methods



















RN2422TE85LF Shipping Methods













If you have any question about RN2422TE85LF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com